

2. (Amended) The surface acoustic wave device according to claim 1, wherein a depth of the region is not more than 50 nm.

3. (Amended) The surface acoustic wave device according to claim 1, wherein the region has a lower resistance than that of an inner portion of the substrate.

4. (Twice Amended) The surface acoustic wave device according to claim 3, wherein a sheet resistance of the region ranges from $10^8 \Omega/\text{square}$ to $10^{15} \Omega/\text{square}$.

5. (Twice Amended) The surface acoustic wave device according to claim 23, wherein the substance is at least one selected from the group consisting of a reducing gas, silane, nitrogen, oxygen, argon, silicon, arsenic, boron, phosphorus, tin, indium, chromium, tantalum, molybdenum, germanium, and nickel.

Please add new claim 23 as follows.

23. (New) The surface acoustic wave device according to claim 1, wherein a substance in at least one form selected from the group consisting of atoms, molecules, clusters, ions and radicals is added to the substrate in the region.
